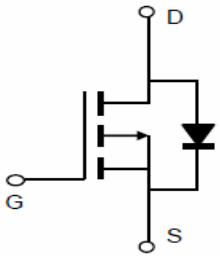
EFMICRO
Semiconductor Limited Company

EFMP307A

P-Channel Advanced Power MOSFET

• Product Summary

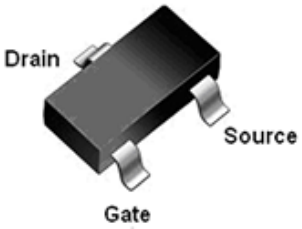
Part #	V_{DS}	$R_{DS(on).typ}$ ($@V_{GS}$=10V)	$R_{DS(on).typ}$ ($@V_{GS}$=4.5V)	I_D
EFMP307A	-30V	23mΩ	35mΩ	-7A



P-Channel MOSFET

• Description

- The EFMP307A is the high cell density trenched
- P-ch MOSFETs which provide excellent
- RDSON and gate cherge for most of the
- synchronous buck converter applications.
- The EFMP307A meet the RoHS and Green
- Prod uct requirement, 100 % EAS guaranteed
- with full function reliability approved.



SOT23-3L

RoHS

HF

•Application

- Super Low Gate Charge 100% EAS Guaranteed
- Green Device Available Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

•Ordering Information:

Part NO.	EFMP307A
Marking	P307A
Packing Information	REEL TAPE
Basic ordering unit (pcs)	3000

•Absolute Maximum Ratings (T_C=25℃)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	-7	A
Drain Current-Pulsed (Note 1)	I_{DM}	-18	A
Maximum Power Dissipation	P_D	1.5	W
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 150	℃

•Thermal Characteristic

Thermal Resistance,Junction-to-Ambient (Note 2)	$R_{\theta JA}$	61.7	℃/W

● Static Electrical Characteristics @ T_J = 25°C (unless otherwise stated)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=-250uA	-30	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-30V V_{GS}=0V	--	--	-1	uA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V V_{DS}=0V	--	--	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS} I_D=-250uA	-1.0	-1.5	-2.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=-10V I_D=-7A	--	23	27	mΩ
		V_{GS}=-4.5VI_D=-4A	--	35	54	mΩ
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=-15V V_{GS}=0V F=1.0MHz	--	982	--	PF
Output Capacitance	C_{oss}		--	135	--	PF
Reverse Transfer Capacitance	C_{rss}		--	109	--	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=-15V I_D=-7A V_{GS}=-10V R_G=2.5Ω,	--	11	--	nS
Turn-on Rise Time	t_r		--	19	--	nS
Turn-Off Delay Time	$t_{d(off)}$		--	45	--	nS
Turn-Off Fall Time	t_f		--	26	--	nS
Total Gate Charge	Q_g	V_{DS}=-15V I_D=-4A V_{GS}=-10V	--	10	--	nC
Gate-Source Charge	Q_{gs}		--	2	--	nC
Gate-Drain Charge	Q_{gd}		--	2.7	--	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V I_S=-7A	--	-0.8	-1.2	V
Diode Forward Current (Note 2)	I_S		--	--	-7	A

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

• Typical Characteristics

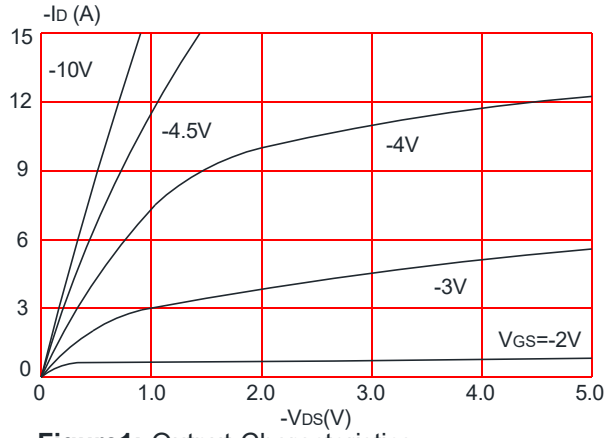


Figure1: Output Characteristics

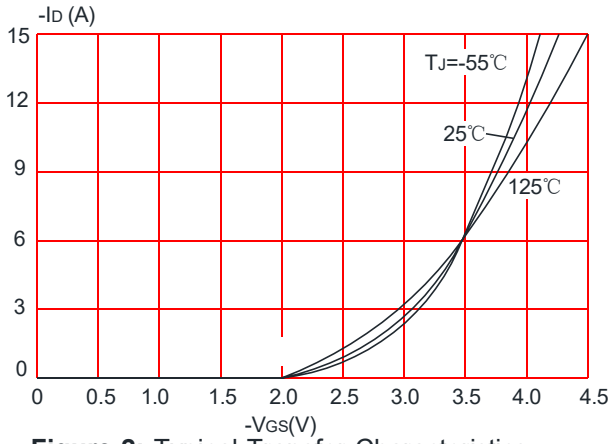


Figure 2: Typical Transfer Characteristics

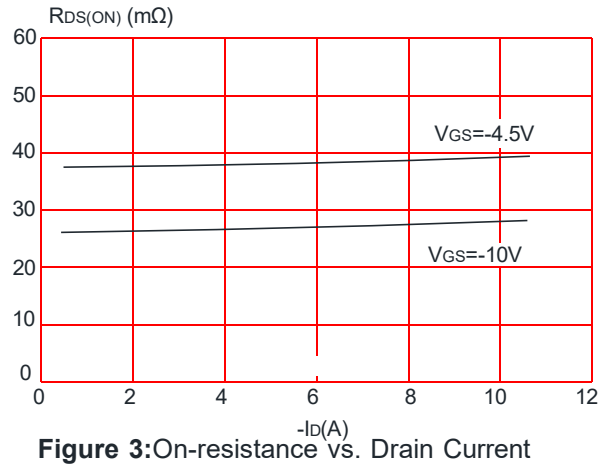


Figure 3: On-resistance vs. Drain Current

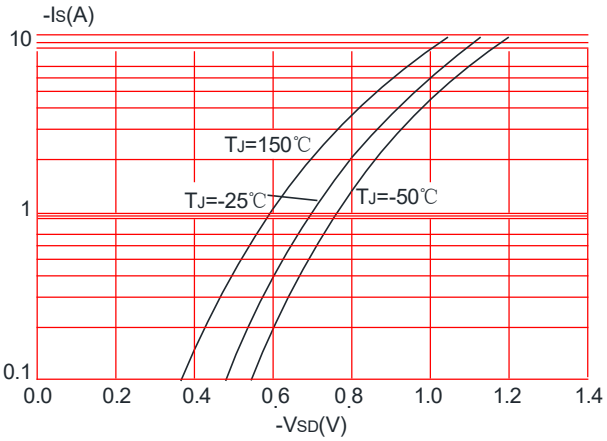


Figure 4: Body Diode Characteristics

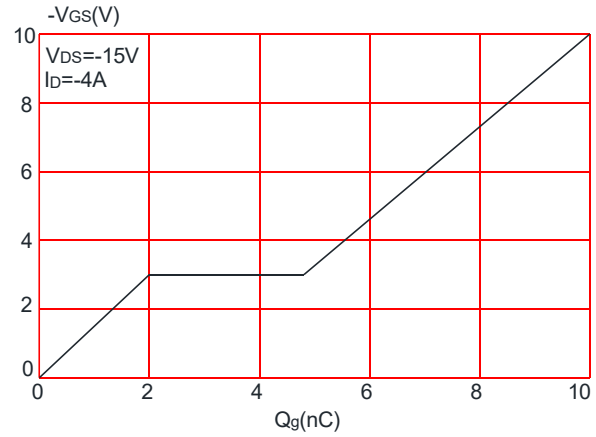


Figure 5: Gate Charge Characteristics

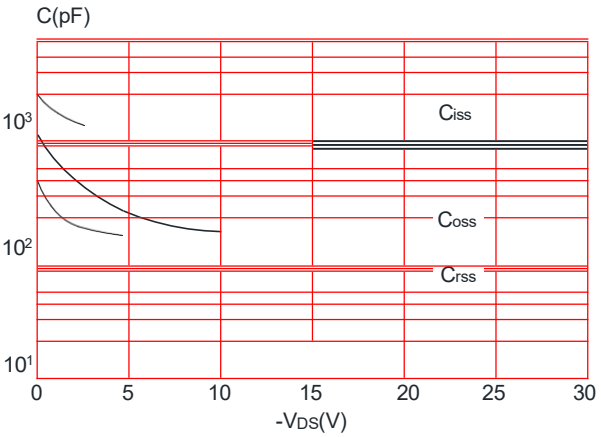


Figure 6: Capacitance Characteristics

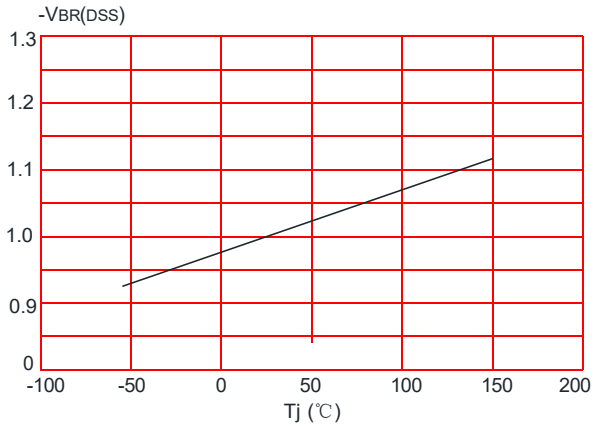


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

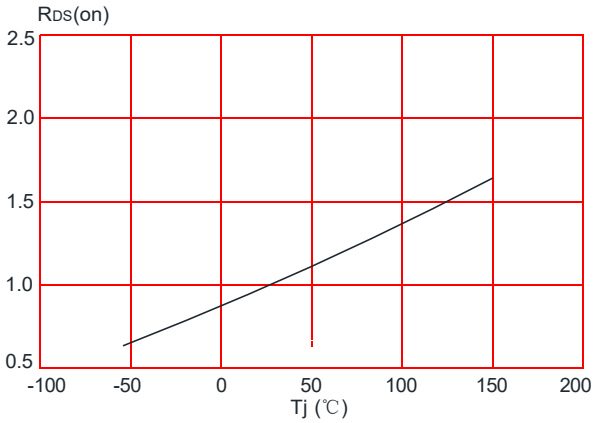


Figure 8: Normalized on Resistance vs. Junction Temperature

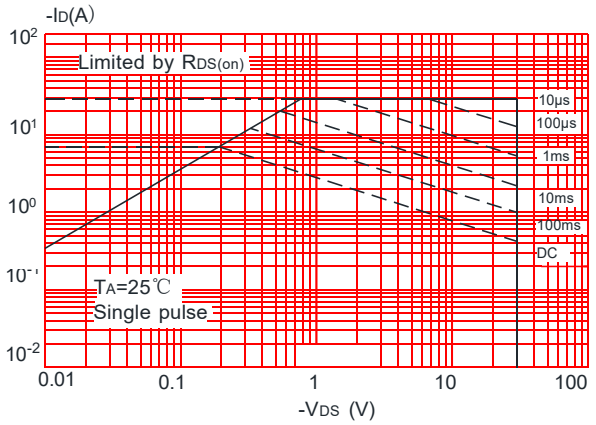


Figure 9: Maximum Safe Operating Area

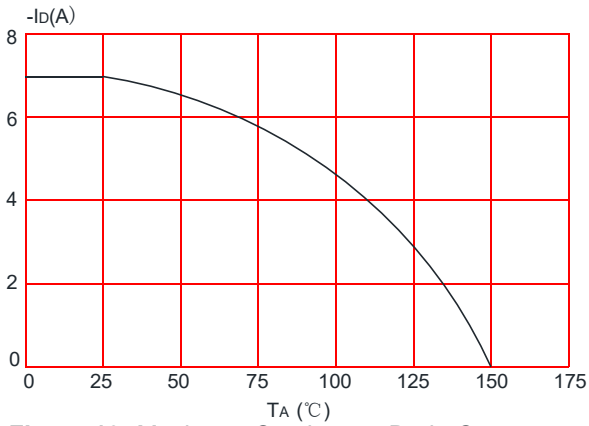


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

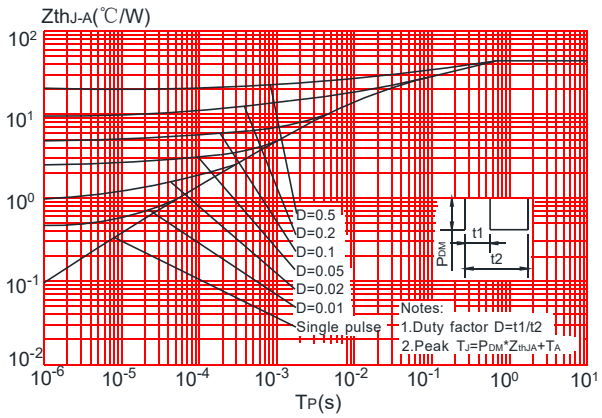
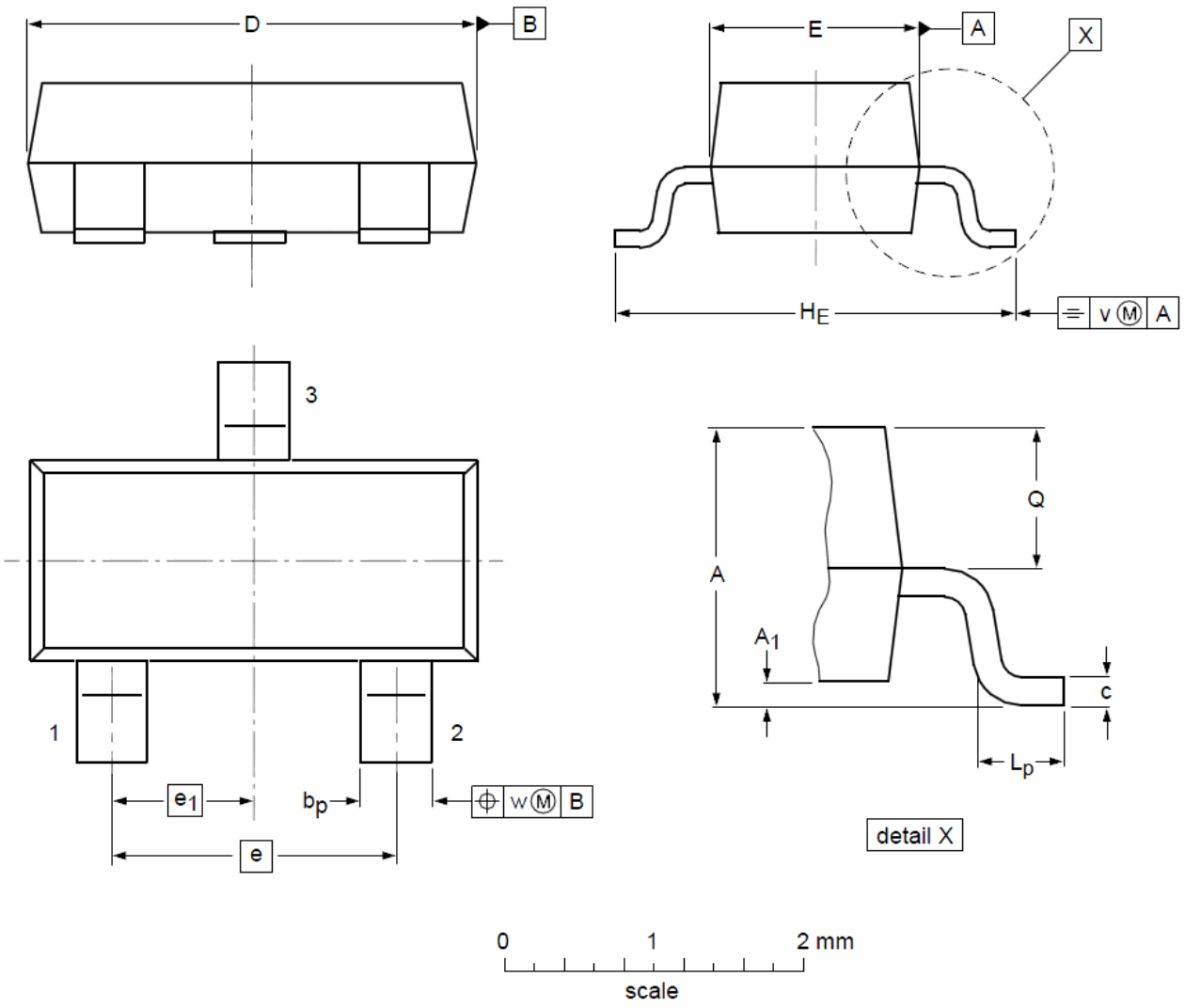


Figure 11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

SOT23-3L Package Outline Dimensions



DIMENSIONS (unit : mm)

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	1.00	1.17	1.30	**A_1**	0.01	0.05	0.10
b_p	0.35	0.39	0.50	**c**	0.10	0.20	0.26
D	2.70	2.90	3.10	**E**	1.30	1.58	1.70
e	--	1.90	--	**e_1**	--	0.95	--
H_E	2.50	2.78	3.00	**L_p**	0.20	0.32	0.60
Q	0.23	0.27	0.33	**v**	--	0.20	--
w	--	0.20	--				